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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
2014	350mΩ @ V _{GS} = -10V	-1.5A
-60V	550mΩ @ V _{GS} = -4.5V	-1.2A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

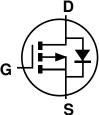
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Mechanical Data

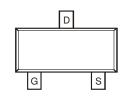
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (63)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)







Internal Schematic



Top View

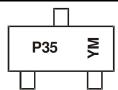
Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP6350S-7	SOT23	3,000/Tape & Reel		
DMP6350S-13	SOT23	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P35 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Date Code (10)									
	Year	2015	2016	2017	2018	2019	2020	2021	2022
	Code	С	D	E	F	G	Н	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6), V _{GS} = -10V	Steady $T_A = +25^\circ$ State $T_A = +70^\circ$	ln ln	-1.5 -1.2	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I _{DM}	-6	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.72	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{ heta JA}$	176	°C/W
Power Dissipation (Note 6)	P_{D}	1.17	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	$R_{ heta JA}$	108	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	34	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

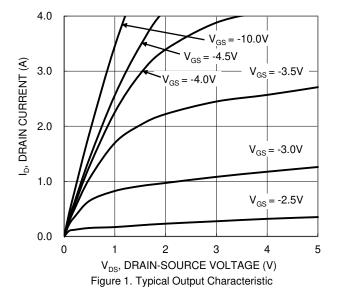
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

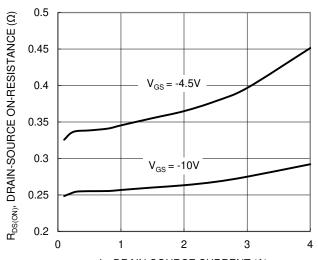
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1.0	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-1.8	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			257	350	mΩ	$V_{GS} = -10V, I_D = -0.9A$	
Static Drain-Source Off-Nesistance	R _{DS(ON)}	-	343	550	11122	$V_{GS} = -4.5V$, $I_D = -0.8A$	
Diode Forward Voltage	V_{SD}	-	-0.8	-1.2	٧	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	206	-	pF		
Output Capacitance	Coss	-	15	-	рF	$V_{DS} = -30V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	11	-	рF	1 = 1.000112	
Gate Resistance	R_{g}	-	17	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	-	2.0	-	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	-	4.1	-	nC	N 201/ 1 0.04	
Gate-Source Charge	Q _{gs}	-	0.5	-	nC	$V_{DS} = -30V, I_{D} = -0.9A$	
Gate-Drain Charge	Q_{gd}	-	0.8	-	nC		
Turn-On Delay Time	t _{D(ON)}	-	3.6	-	ns		
Turn-On Rise Time	t _R	-	3.8	-	ns	$V_{DD} = -30V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	-	12.3	-	ns	$I_D = -1.0A$, $R_g = 6\Omega$	
Turn-Off Fall Time	t _F	-	7.3	-	ns	7	
Body Diode Reverse Recovery Time	t _{RR}	-	8.2	-	ns	$I_S = -1.0A$, $di/dt = -100A/\mu s$	
Body Diode Reverse Recovery Charge	Q_{RR}	-	2.7	-	nC	$I_S = -1.0A$, di/dt = -100A/ μ s	

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

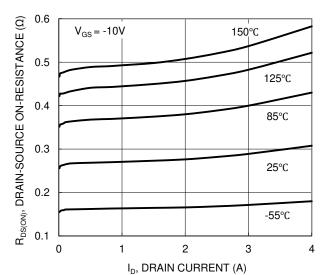
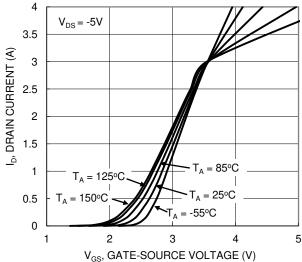


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



 V_{GS} , GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

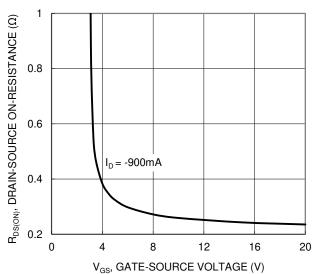


Figure 4. Typical Transfer Characteristic

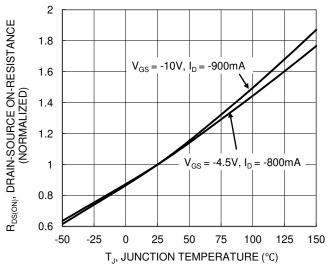


Figure 6. On-Resistance Variation with Junction Temperature



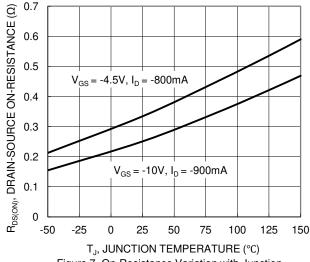
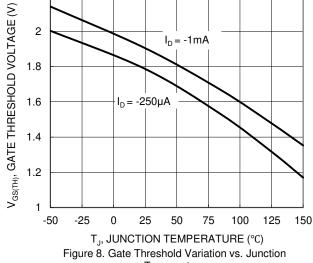


Figure 7. On-Resistance Variation with Junction Temperature



2.2

Temperature

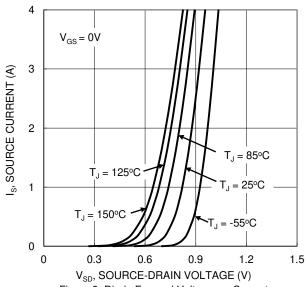
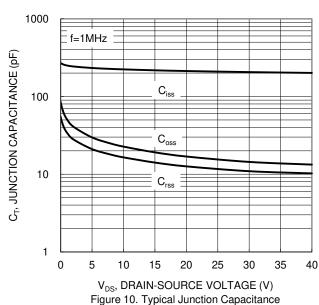
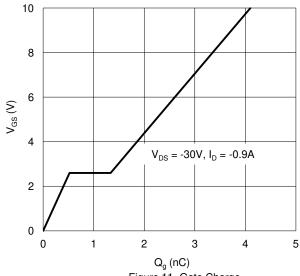


Figure 9. Diode Forward Voltage vs. Current



10 ____ $\boldsymbol{R}_{DS(ON)}$ Limited =100µs ID, DRAIN CURRENT (A) P_{W} 0.1 $T_{J(Max)} = 150^{\circ}C$ $T_C = 25^{\circ}C$ 0.01 Single Pulse DUT on 1*MRP Board $V_{GS} = -10V$ 0.001 0.1 10 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



100



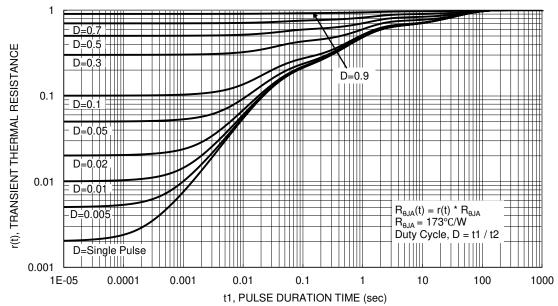


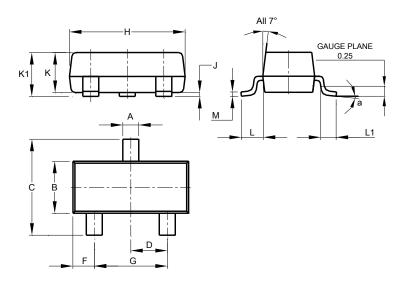
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT23

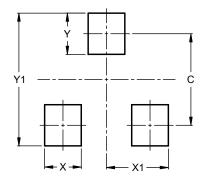


	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9

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